

Fida Ali

List of Publications by Year in descending order

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14
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485
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical characterization of 2D materials-based field-effect transistors. 2D Materials, 2021, 8, 012002.	2.0	111
2	Gate-Modulated Ultrasensitive Visible and Near-Infrared Photodetection of Oxygen Plasma-Treated WSe ₂ Lateral pn-Homojunctions. ACS Applied Materials & Interfaces, 2020, 12, 23261-23271.	4.0	41
3	Resonant tunnelling diodes based on twisted black phosphorus homostructures. Nature Electronics, 2021, 4, 269-276.	13.1	41
4	Dielectric Dispersion and High Field Response of Multilayer Hexagonal Boron Nitride. Advanced Functional Materials, 2018, 28, 1804235.	7.8	38
5	Fermi-Level Pinning Free High-Performance 2D CMOS Inverter Fabricated with Van Der Waals Bottom Contacts. Advanced Electronic Materials, 2021, 7, 2001212.	2.6	28
6	Phase-Engineered Molybdenum Telluride/Black Phosphorus Van der Waals Heterojunctions for Tunable Multivalued Logic. ACS Applied Materials & Interfaces, 2020, 12, 14119-14124.	4.0	27
7	Control of the Schottky Barrier and Contact Resistance at Metal/WSe ₂ Interfaces by Polymeric Doping. Advanced Electronic Materials, 2020, 6, 2000616.	2.6	24
8	Energy Dissipation in Black Phosphorus Heterostructured Devices. Advanced Materials Interfaces, 2019, 6, 1801528.	1.9	14
9	Traps at the hBN/WSe ₂ interface and their impact on polarity transition in WSe ₂ . 2D Materials, 2021, 8, 035027.	2.0	13
10	Metal-Insulator Transition Driven by Traps in 2D WSe ₂ Field-Effect Transistor. Advanced Electronic Materials, 2022, 8, .	2.6	8
11	Anomalously persistent p-type behavior of WSe ₂ field-effect transistors by oxidized edge-induced Fermi-level pinning. Journal of Materials Chemistry C, 2022, 10, 846-853.	2.7	5
12	Ultrahigh Anisotropic Transport Properties of Black Phosphorus Field Effect Transistors Realized by Edge Contact. Advanced Electronic Materials, 2022, 8, .	2.6	5
13	Interface state density and barrier height improvement in ammonium sulfide treated Al ₂ O ₃ /Si interfaces. Current Applied Physics, 2021, 26, 83-89.	1.1	0